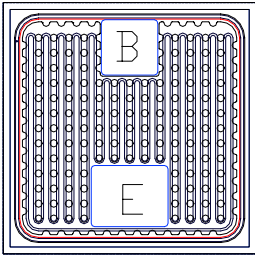


D882B Silicon NPN Epitaxial Transistor

Description :The D882B is designed for use in output stage of 1w audio amplifier, voltage regulator, DC-DC converter and relay driver.

Features: ●Excellent h_{FE} Linearity
 ●Complementary to B772B

Chip Appearance

	Chip Size		1100um × 1100um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	240um × 240um
		Emitter	330um × 260um
	Front Metal		Al
	Backside Metal		Au (As) /TiNiAg
	Scribe line width		60um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=35V, I_E=0$		0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=0.1mA$	40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA$	30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=0.1mA$	5.0		V
DC Current Gain	h_{FE}	$V_{CE}=2V, I_C=1A$	100	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=200mA$		0.5	V